

## **TN6727A**



# **PNP General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1A. Sourced from Process 77. See TN6726A for characteristics.

### Absolute Maximum Ratings\*

T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current - Continuous	1.5	Α
T <sub>J, ⊺stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES

### Thermal Characteristics \_\_\_ T\_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN6727A	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	1 8	W mW/°C
R <sub>0</sub> JC	Thermal Resistance, Junction to Case	50	°C/W
R <sub>θ</sub> JA	Thermal Resistance, Junction to Ambient	125	°C/W

<sup>1)</sup> These ratings are based on a maximum junction temperature of 150°C.

<sup>2)</sup> These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# **PNP General Purpose Amplifier**

(continued)

### **Electrical Characteristics**

 $T_{A\,=\,25^{\circ}\text{C unless otherwise noted}}$ 

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA	40		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1 mA	50		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1 mA	5		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 50 V		100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5 V		100	nA
ON CHAI	RACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 1A, V_{CE} = 1 \text{ V}$	55 60 50	250	-
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1 A, V <sub>CE</sub> = 1 V		1.2	V
SMALL S	IGNAL CHARACTERISTICS				
C <sub>cb</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1MHz		30	pF
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 50 mA,V <sub>CE</sub> = 10 V, f=20MHz	2.5	25	-

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  1.0%

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